

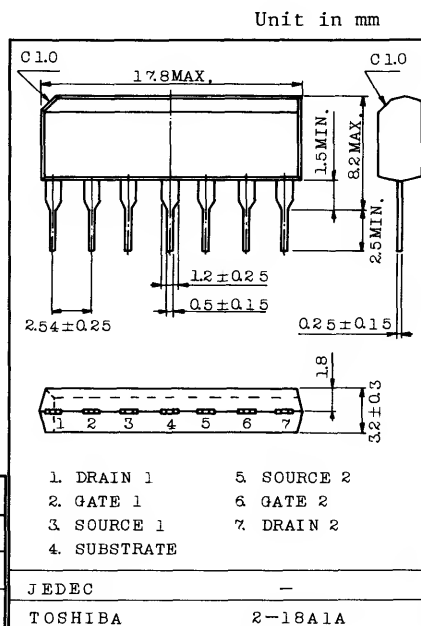
LOW NOISE AUDIO AND DIFFERENTIAL
AMPLIFIER APPLICATIONS.

FEATURES:

- . 1 Chip Dual Type.
- . Recommended for First Differential Stages of DC Amplifiers.
- . Very High $|Y_{fs}|$: $|Y_{fs}| = 20\text{mS}(\text{Typ.})$
($V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{kHz}$, $I_{DSS}=3\text{mA}$)
- . Good Pair Characteristics :
 $|V_{GS1}-V_{GS2}|=30\text{mV}(\text{Max.})$ ($V_{DS}=10\text{V}$, $I_D=1\text{mA}$)
- . High Breakdown Voltage : $V_{GDS}=-40(\text{Min.})$
- . Very Low Noise : $\text{NF}=0.5\text{dB}(\text{Typ.})$
($V_{DS}=10\text{V}$, $I_D=1\text{mA}$, $R_g=1\text{k}\Omega$, $f=1\text{kHz}$)
- . High Input Impedance : $I_{GSS}=-10\text{nA}(\text{Max.})$ ($V_{GS}=-30\text{V}$)
- . Complementary to 2SJ90.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	300	mW/ UNIT
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ 125	$^\circ\text{C}$



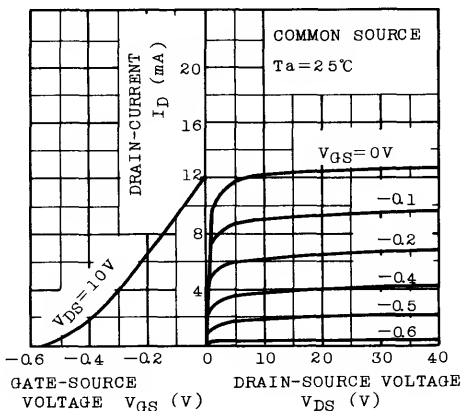
Weight : 0.7g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

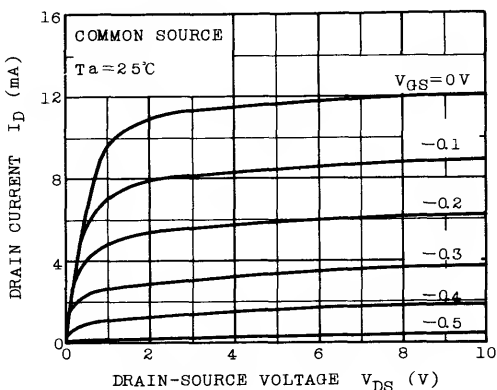
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS}=-30\text{V}$, $V_{DS}=0$	-	-	-10	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS}=0$, $I_G=-100\mu\text{A}$	-40	-	-	V
Drain Current	I_{DSS} (Note)	$V_{DS}=10\text{V}$, $V_{GS}=0$	1	-	20	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS}=10\text{V}$, $I_D=0.1\mu\text{A}$	-0.2	-	-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{kHz}$, $I_{DSS}=3\text{mA}$	8	20	-	mS
Forward Transfer Admittance Ratio	$ Y_{fs(\text{小})} / Y_{fs(\text{大})} $	$V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{kHz}$	0.9	-	-	-
Differential Gate Voltage	$ V_{GS1} - V_{GS2} $	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	-	-	30	mV
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{MHz}$	-	25	-	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DG}=10\text{V}$, $I_D=0$, $f=1\text{MHz}$	-	5.5	-	pF
Noise Figure	NF (1)	$V_{DS}=10\text{V}$, $R_g=1\text{k}\Omega$, $I_D=1\text{mA}$, $f=10\text{Hz}$	-	-	11	dB
	NF (2)	$V_{DS}=10\text{V}$, $R_g=1\text{k}\Omega$, $I_D=1\text{mA}$, $f=1\text{kHz}$	-	-	2	

Note : I_{DSS} Classification Y:1.0 ~ 3.0mA, GR:2.6 ~ 6.5mA, BL:6 ~ 12mA, V:10 ~ 20mA

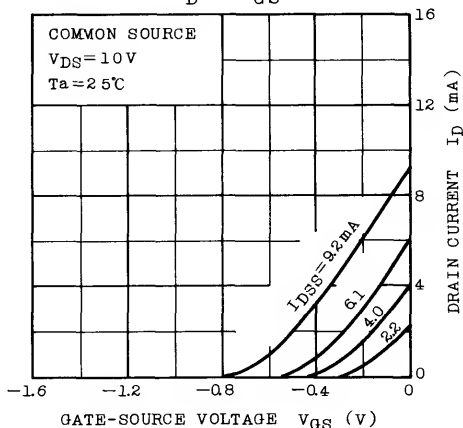
STATIC CHARACTERISTICS



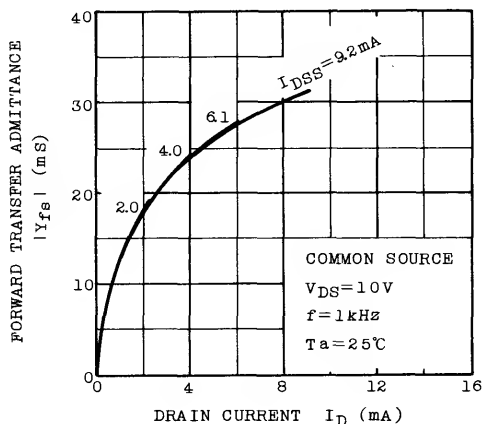
ID - VDS (LOW VOLTAGE REGION)



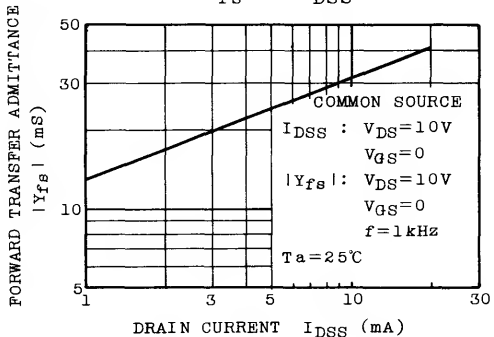
ID - VGS



|Yfs| - ID



|Yfs| - IDSS



VGS(OFF) - IDSS

